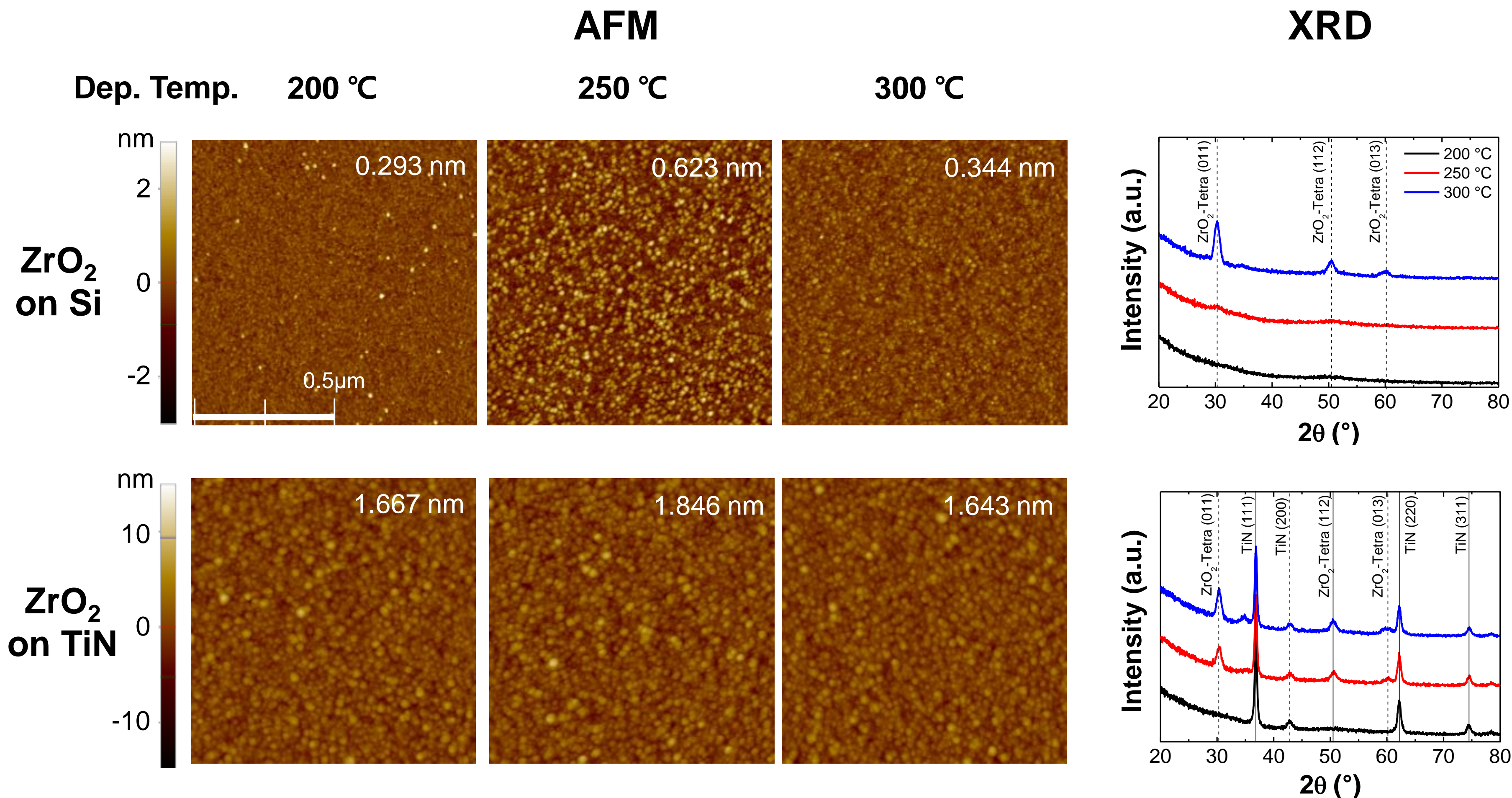
Characterization of ALD-ZrO_2 (Target: 10nm) Thin Film on ALD-TiN / Si Using O_3 - AFM, XRD



- Maximum RMS at 250°C deposition temperature
- As the deposition temperature increases, more crystallization occurs in ZrO_2